

Schottky Power Rectifier

Surface Mount Power Package

MBRS1100T3G, SBR81100T3G, MBRS190T3G, SBR8190T3G, SBR81100N, SBR8190N

Schottky Power Rectifiers employ the use of the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes, in surface mount applications where compact size and weight are critical to the system. These state-of-the-art devices have the following features:

Features

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- High Blocking Voltage – 100 Volts
- 175°C Operating Junction Temperature
- Guardring for Stress Protection
- AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in 12 mm Tape and Reel, 2,500 units per reel
- Cathode Polarity Band



ON Semiconductor®

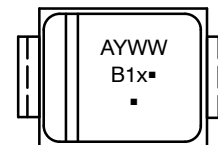
www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE 90, 100 VOLTS



**SMB
CASE 403A**

MARKING DIAGRAM



- B1 = Device Code
- x = C for MBR81100T3
9 for MBR8190T3
- A = Assembly Location**
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

**The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G, SBRS81100N, SBRS8190N

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBRS190T3 MBRS1100T3	V_{RRM} V_{RWM} V_R	90 100	V
Average Rectified Forward Current $T_L = 163^\circ\text{C}$ $T_L = 148^\circ\text{C}$	$I_{F(AV)}$	1.0 2.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	50	A
Operating Junction Temperature (Note 1)	T_J	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change	dv/dt	10	V/ns

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead ($T_L = 25^\circ\text{C}$)	$R_{\theta JL}$	22	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 1.0\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	0.75	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 100^\circ\text{C}$)	I_R	0.5 5.0	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MBRS1100T3G	B1C	SMB (Pb-Free)	2500 / Tape & Reel
SBRS81100T3G*	B1C	SMB (Pb-Free)	2500 / Tape & Reel
SBRS81100T3G-VF01*	B1C	SMB (Pb-Free)	2500 / Tape & Reel
MBRS190T3G	B19	SMB (Pb-Free)	2500 / Tape & Reel
SBRS8190T3G*	B19	SMB (Pb-Free)	2500 / Tape & Reel
SBRS81100NT3G*	B1C	SMB (Pb-Free)	2500 / Tape & Reel
SBRS8190NT3G*	B19	SMB (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SBRS8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

MBRS1100T3G, SBRS81100T3G, MBRS190T3G, SBRS8190T3G, SBRS81100N, SBRS8190N

TYPICAL ELECTRICAL CHARACTERISTICS

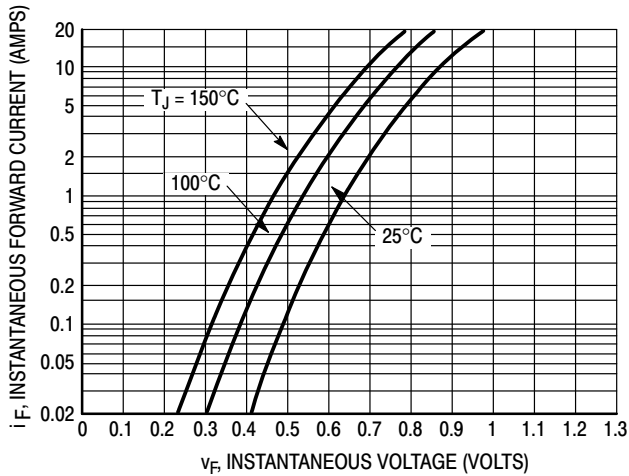


Figure 1. Typical Forward Voltage

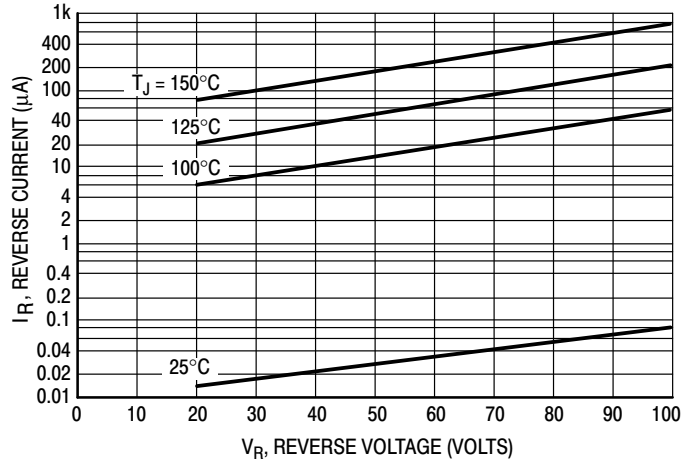


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R .

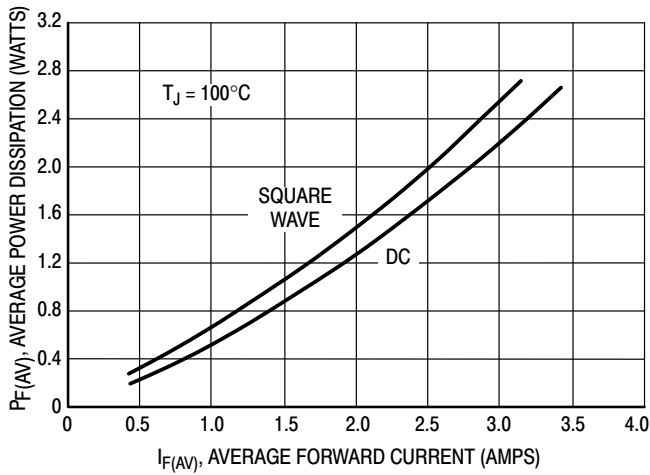


Figure 3. Power Dissipation

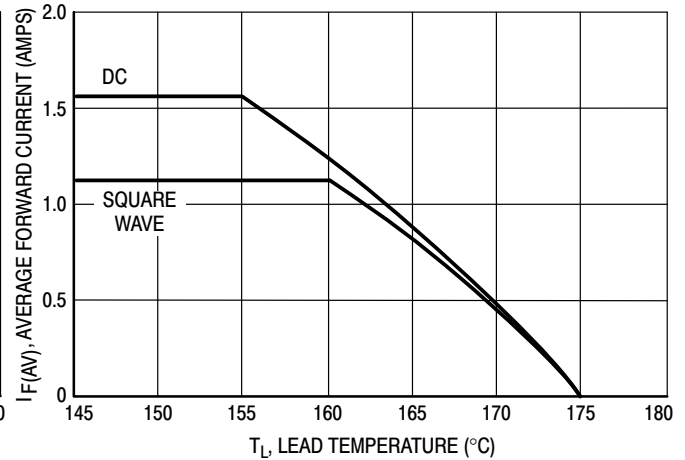


Figure 4. Current Derating, Lead

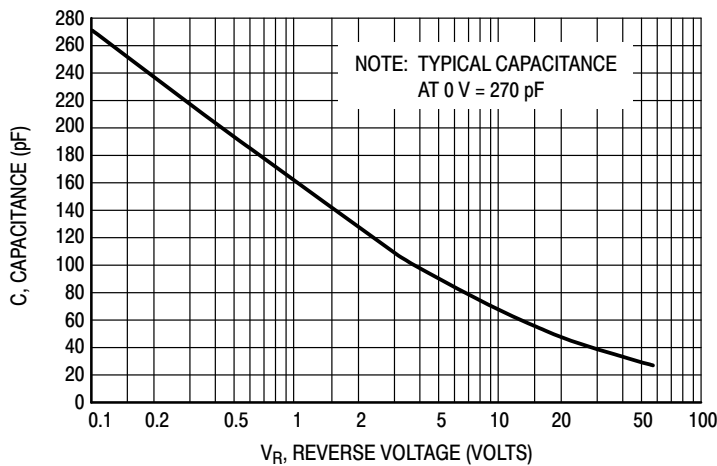


Figure 5. Typical Capacitance

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

Polarity Band

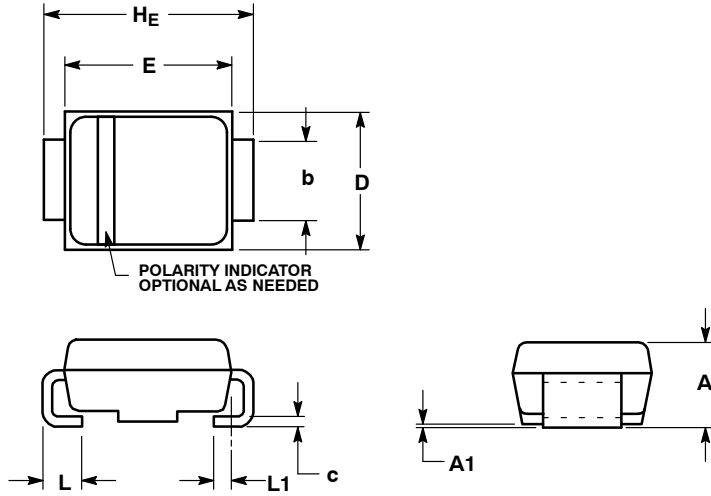


SCALE 1:1

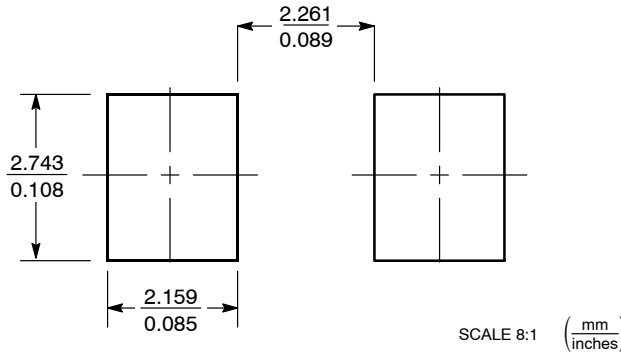
Non-Polarity Band

SMB
CASE 403A-03
ISSUE J

DATE 19 JUL 2012



SOLDERING FOOTPRINT*

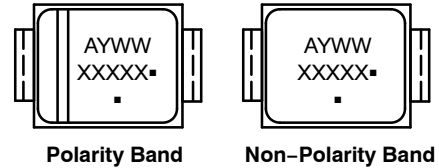


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.95	2.30	2.47	0.077	0.091	0.097
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
HE	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
 - A = Assembly Location
 - Y = Year
 - WW = Work Week
 - = Pb-Free Package
- (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASB42669B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SMB	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

[MBRS1100T3](#) [MBRS1100T3G](#) [MBRS190T3](#) [MBRS190T3G](#) [SBRS81100T3G](#) [SBRS8190T3G](#) [SBRS81100T3G-VF01](#) [SBRS8190T3G-VF01](#) [SBRS8190T3](#) [SBRS81100NT3G](#) [SBRS8190NT3G](#)